

isc Silicon NPN Darlington Power Transistor

2SD837

DESCRIPTION

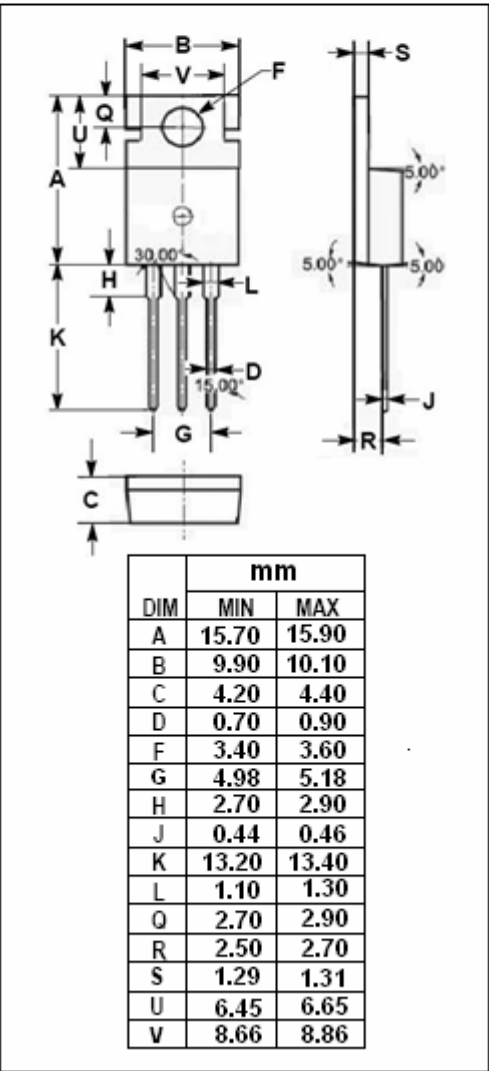
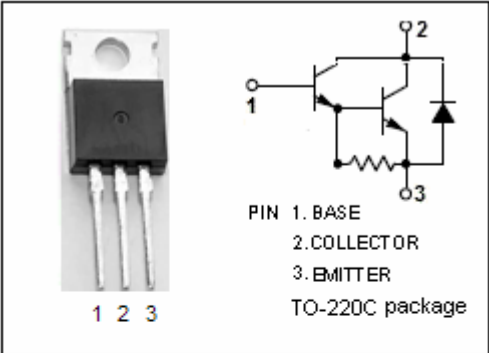
- High DC Current Gain-
: $h_{FE}=1000(\text{Min.})@I_C=3A$
- High Switching Speed

APPLICATIONS

- Audio power amplifiers
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Base Current-Peak	8	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	40	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Darlington Power Transistor**2SD837****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA ; I _B = 0	60			V
V _{CE(sat)} -1	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 12mA			2	V
V _{CE(sat)} -2	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 20mA			4	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 3A ; V _{CE} = 3V			2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			0.2	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 30V; I _B = 0			0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0			2	μ A
h _{FE-1}	DC Current Gain	I _C = 0.5A ; V _{CE} = 3V	1000			
h _{FE-2}	DC Current Gain	I _C = 3A ; V _{CE} = 3V	1000		10000	

Switching Times

t _{on}	Turn-On Time	I _C = 3A; I _{B1} = -I _{B2} = 12mA		0.3		μ s
t _{off}	Turn-Off Time			4		μ s